GBJ2516A

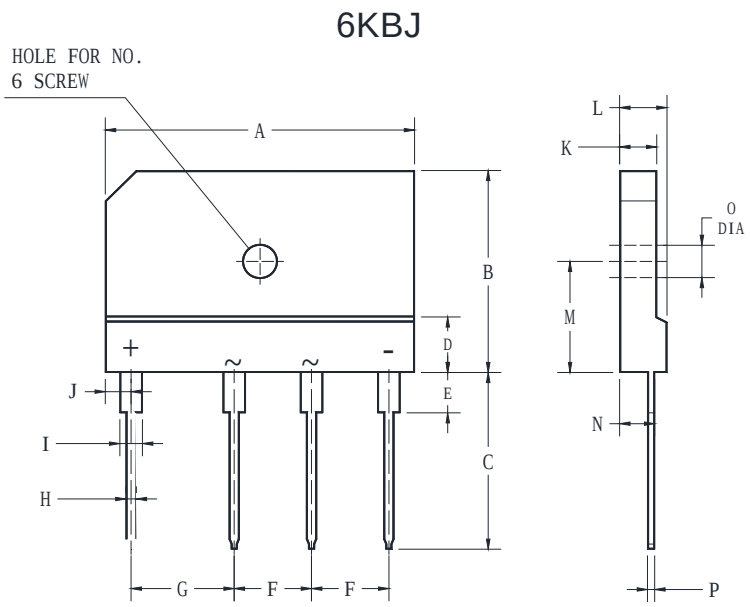
■Maximum Ratings (T_a=25 Unless otherwise specified

PARAMETER		SYMBOL	UNIT	GBJ2516A
Device marking code				GBJ2516A
Maximum Repetitive Peak Reverse Voltage		V_{RRM}	V	1600
Maximum RMS Voltage		V_{RMS}	V	1120
Maximum DC blocking Voltage		V_{DC}	V	1600
Average rectified output current @60Hz sine wave, R-load,	With heatsink Tc =95	I_O	A	25.0
	Without heatsink Ta =25			3.5
Forward Surge Current (Non-repetitive) @60Hz Half-sine wave,1 cycle, Tj=25		I_{FSM}	A	350
Forward Surge Current (Non-repetitive) @1ms, square wave, 1 cycle, Tj=25				700
Current squared time @1ms≤t≤8.3ms Tj=25 , Rating of per diode		I^2t	A^2s	508
Storage temperature		T_{stg}		-55 ~ +150
Junction temperature		T_j		-55 ~ +150
Dielectric strength @ Terminals to case, AC 1 minute		V_{dis}	KV	2.5
Mounting torque @Recommend torque 5kg cm		Tor	kg cm	8

■Electrical Characteristics T_a=25 Unless otherwise specified

PARAMETER	SYMBOL	UNIT	TEST CONDITIONS	GBJ2516A
Maximum instantaneous forward voltage drop per diode	V_F	V	I_{FM}=12.5A	1.1
Maximum DC reverse current at rated DC blocking voltage per diode	I_R	μA	T_j=25	5
			T_j=125	5-. b d ʖ

■ Outline Dimensions



Dimensions in millimeters

6KBJ		
Dim	Min	Max
A	29.7	30.3
B	19.7	20.3
C	17.0	18.0
D	4.8	5.8
E	3.8	4.2
F	7.3	7.7
G	9.8	10.2
H	0.9	1.1
I	2.0	2.4
J	2.3	2.7
K	3.4	3.8
L	4.4	4.8
M	10.8	11.2
N	3.1	3.7
O	3.1	3.4
P	0.6	0.8

Disclaimer

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The product listed herein is designed to be used with ordinary electronic equipment or devices, and not designed to be used with equipment or devices which require high level of reliability and the malfunction of with would directly endanger human life (such as medical instruments, transportat